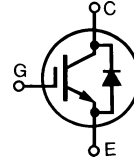


High Voltage IGBT with Diode

IXSK 35N120BD1
IXSX 35N120BD1

$V_{CES} = 1200\text{ V}$
 $I_{C25} = 70\text{ A}$
 $V_{CE(SAT)} = 3.6\text{ V}$

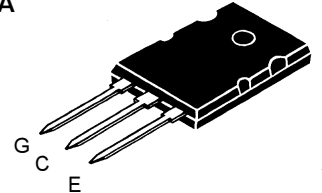
Short Circuit SOA Capability



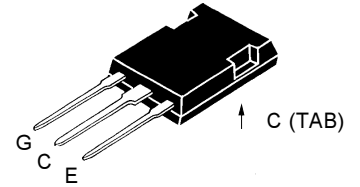
Preliminary data sheet

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1\text{ M}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	70	A
I_{C90}	$T_C = 90^\circ\text{C}$	35	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ ms}$	140	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}, T_J = 125^\circ\text{C}, R_G = 5\ \Omega$ Clamped inductive load	$I_{CM} = 90$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15\text{ V}, V_{CE} = 720\text{ V}, T_J = 125^\circ\text{C}$ $R_G = 5\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT	300 W
		Diode	190 W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 AA (IXSK)



PLUS TO-247™ (IXSX)



G = Gate,
E = Emitter,

C = Collector,
TAB = Collector

Features

- Hole-less TO-247 package for clip mounting
- High frequency IGBT and anti-parallel FRED in one package
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

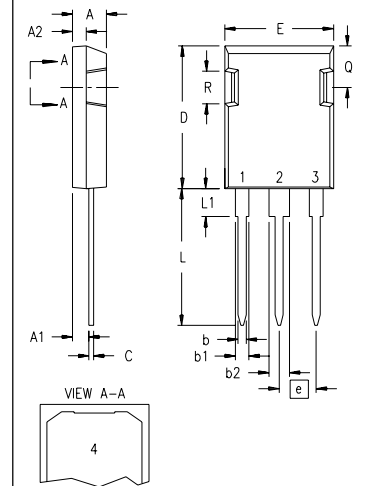
- Space savings (two devices in one package)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 3\text{ mA}, V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	3		V
I_{CES} ①	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$ $T_J = 125^\circ\text{C}$			1 mA 3 mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15\text{ V}$			3.6 V

① Device must be heatsunk for high temperature measurements to avoid thermal runaway.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	16	23	S	
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		3600	pF	
C_{oes}			315	pF	
C_{res}			75	pF	
Q_g	I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		120	nC	
Q_{ge}			33	nC	
Q_{gc}			49	nC	
t_{d(on)}	Inductive load, T_J = 25°C I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.8 V _{CES} ; R _G = 5.0 Ω Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		36	ns	
t_{ri}			27	ns	
t_{d(off)}			160	300	ns
t_{fi}			180	300	ns
E_{off}			5	9	mJ
t_{d(on)}	Inductive load, T_J = 125°C I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.8 V _{CES} ; R _G = 5.0 Ω Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		38	ns	
t_{ri}			29	ns	
E_{on}			6	mJ	
t_{d(off)}			240	ns	
t_{fi}			340	ns	
E_{off}		9	mJ		
R_{thJC}				0.42 KW	
R_{thCK}		0.15		KW	

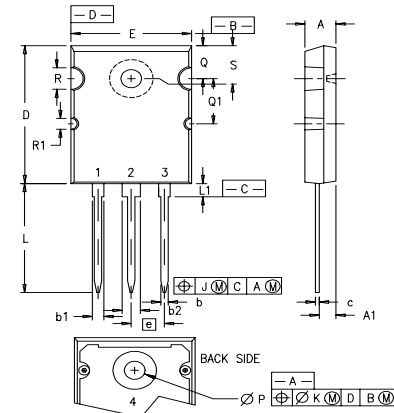
TO-247 HOLE-LESS Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

TO-264 AA Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

- 1 - GATE
- 2, 4 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	I _F = 130A, V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %, T _J = 125°C			2.75 V 1.85 V
I_{RM}	I _F = 130A, V _{GE} = 0 V, -di _F /dt = 100 A/μs, T _J = 100°C V _R = 100 V		7	14.3 A
t_{rr}		I _F = 1 A; -di _F /dt = 200 A/μs; V _R = 30 V		40
R_{thJC}				0.65 KW

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025